High Dynamic Range Low Noise GaAs FET



August 2006 - Rev 03-Aug-06 **CFB0301**

Features

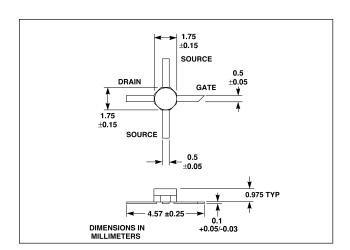
- ☐ Low-Noise Figure from 0.8 to 2.0 GHz
- ☐ High Gain
- ☐ High Intercept Point
- ☐ Highly Stable
- \Box Easily Matched to 50Ω
- ☐ 70 mil Package

Applications

- **□** Cellular Base Stations
- **□** PCS Base Stations
- Industrial Data Networks

Description

Celeritek's CFB0301 is a high performance GaAs MESFET with 600 μm gate width and 0.25 μm gate length. The low noise figure and high intercept point of this device makes it well suited for use as the low-noise amplifier of the



base station receiver in PCS, Japanese PHS, AMPS, GSM and other communications systems. The CFB0301 is in an industry-standard 70 mil package. It is surface mountable and available in tape and reel.

Electrical Specifications (TA = 25°C, 2 GHz)

Parameters	Conditions	Min	Тур	Standard Deviation ⁴	Max	Units
$\overline{V_d} = 2V, I_d = 25 \text{ mA}$			-71			
Noise Figure ²			0.6			dB
Associated Gain ²	@ Noise Figure		16			dB
P _{out} 1, 3	P ₋₁		15.0			dBm
$\overline{\text{IP}_3}^3$	+5 dBm P _{OUT} /Tone		24			dBm
P _{out} 1, 3 IP ₃ 3 Id 3	@ P ₋₁		35			mA
$\overline{V_d} = 4V, I_d = 30 \text{ mA}$	•					
Noise Figure ² Associated Gain ²			0.7			dB
Associated Gain ²	@ Noise Figure		17			dB
P _{out} 1, 3	P ₋₁		20.5			dBm
$\overline{\text{IP}_3}^3$	+5 dBm P _{OUT} /Tone		30			dBm
$\frac{\frac{\text{IP}_3}{3}}{\frac{\text{Id}}{3}}$	@ P ₋₁		56			mA
$\overline{V_d} = 4V, I_d = 70 \text{ mA}$						
Noise Figure ²			0.8	0.08	0.9	dB
Associated Gain ²	@ Noise Figure	16	17	0.4		dB
P _{out} 1, 3	P ₋₁	20	21	0.4		dBm
Pout 1, 3 IP ₃ 3	+5 dBm P _{OUT} /Tone	32	34	0.9		dBm
I_d^3	@ P ₋₁		77			mA
Transconductance	$V_{ds} = 2 \text{ V}, V_{gs} = 0 \text{ V}$	70	140			mho
Saturated Drain Current	$V_{ds} = 2 \text{ V}, V_{gs} = 0 \text{ V}$	120	150		180	mA
Pinchoff Voltages	$V_{ds} = 2 \text{ V}, I_{ds} = 1 \text{ mA}$	-2.5	-1.3		-0.5	V
Thermal Resistance	@ T _{case} = 150°C liquid crystal test		200			°C/W

Notes: 1. @ $T_{case} = 25^{\circ}C$. Derate 5 mW/°C for $T_{case} > 25^{\circ}C$. 2. Input matched for low noise. 3. Matched for power transfer.

4. Standard deviation based on 10 wafers randomly selected and is provided as an estimate of the distribution only. Trademarks are the property of their respected owners.



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Typical Noise Parameters $(V_{ds} = 4 \text{ V}, I_{ds} = 30 \text{ mA})$

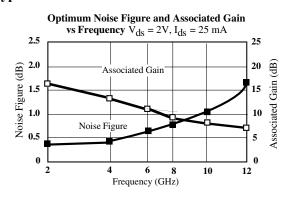
Frequency	F _{min} ¹	Gamn	na Opt			
(GHz)	(dB)	Mag	Ang	Rn/50		
0.8	0.4	0.6	27	0.19		
1.0	0.4	0.6	29	0.17		
1.2	0.4	0.6	32	0.18		
1.4	0.4	0.6	35	0.18		
1.6	0.4	0.5	38	0.17		
1.8	0.4	0.5	41	0.16		
2.0	0.5	0.5	45	0.15		
2.2	0.5	0.5	49	0.15		
2.4	0.5	0.5	54	0.14		
2.6	0.5	0.5	60	0.13		

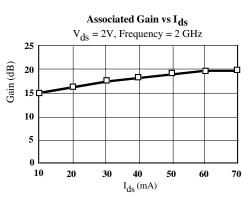
Note: 1. Fmin values reflect the circuit losses in the test fixture when matched to optimum noise figure.

Absolute Maximum Ratings

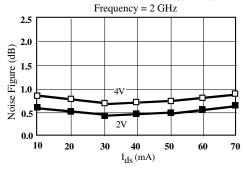
Parameter	Symbol	Rating
Drain-Source Voltage	v _{ds}	+8V
Gate-Source Voltage		-5V
Drain Current	${ m V}_{ m gs} \ { m I}_{ m ds}$	Idss
Continuous Dissipation ¹	Pt	750 mW
Channel Temperature	Tch	175°C
Storage Temperature	Tstg	-65°C to +150°C

Typical Performance





Optimum Noise Figure vs $\mathbf{I}_{ds} \, \& \, \mathbf{V}_{ds}$



Typical Scattering Parameters (TA = 25° C, $V_{DS} = 2$ V, $I_{DS} = 25$ mA)

	_		D5	20				
Frequency	S ₁₁		s ₂₁		S ₁₂		S ₂₂	
(GHz)	Mag	Ang	Mag (dB)	Ang	MAG (dB)	ANG	MAG	ANG
0.5	0.98	-20	7.17	161	0.02	78	0.42	-11
1.0	0.94	-40	6.90	148	0.03	70	0.41	-24
2.0	0.85	-76	6.00	119	0.05	52	0.36	-46
3.0	0.76	-108	5.00	95	0.07	38	0.32	-65
4.0	0.70	-130	4.30	75	0.08	30	0.30	-75
5.0	0.64	-150	3.83	55	0.09	20	0.27	-85

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Test Circuit Evaluation Board Schematic

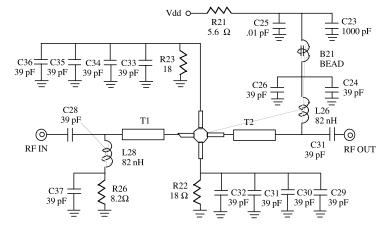
Evaluation Board Substrate:

ER = 4.65

Thickness = 0.036

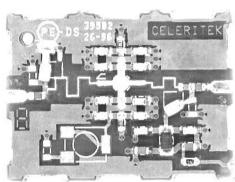
Transmission Lines (Dimensions in mm.):

T1: 0.203 (W) x 11.55 (L) T2: 0.203 (W) x 5.05 (L)



PB-CFB0301 Evaluation Board

(SMA Connectors not shown)



Evaluation Board Parts List

Item	Reference Designator	Description	Quantity	Manufacturer	Part Number
1	B21	Chip ferrite bead 0805	1	World Products	HB-1H2012-260JT
2	C23	Capacitor, 1000pF, 0603	1	Rohm	MCH185A102JK
3	C21, C24, C26, C28-C37	Capacitor, 39pF, 0603	13	Rohm	MCH185A039JK
4	C25	Capacitor, 0.01µF, 0603	1	Rohm	MCH185A103JK
5	L26, L28	Inductor, 82nH, INDA5T-3	2	Toko	LL2012-F8NK
6	R21	Resistor, 5.6 Ohm, 0603	1	Dale	RCWP575 560
7	R22, R23	Resistor, 18 Ohm, 0603	2	Dale	RCWP575 181
8	R26	Resistor, 8.2 Ohm, 0603	1	Dale	RCWP575 820

Ordering Information

The CFB0301GaAs FET is available in tape and reel. An evaluation board is also available. Ordering part numbers are listed.

<u>Part Number for Ordering</u> <u>Function</u> <u>Package</u>

CFB0301 Low-Noise high dynamic range FET 70 mil package

CFB0301-000T Low-Noise high dynamic range FET 70 mil package in tape and reel

PB-CFB0301 Evaluation Board

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